



## **High power microwave and millimeter wave rectennas based on a highly scaled GaN rectifier technology**

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The presentation will focus on new advancements in high power rectenna circuits using a newly developed GaN nanoSchottky diode. Its' DC and RF performance and capabilities will be discussed and compared to the currently available diode rectifiers. The millimeter wave rectenna performance will also be discussed , highlighting its RF-DC efficiency and ultra-high power capability.